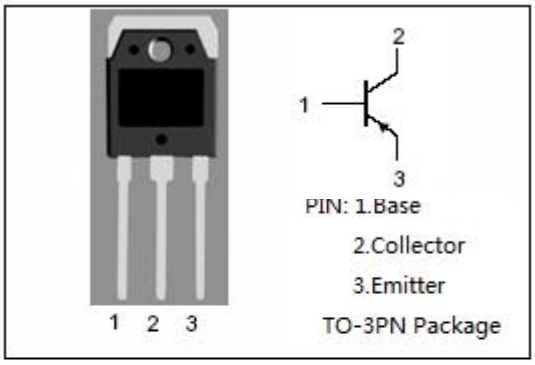
isc Silicon PNP Power Transistor 2SB1345

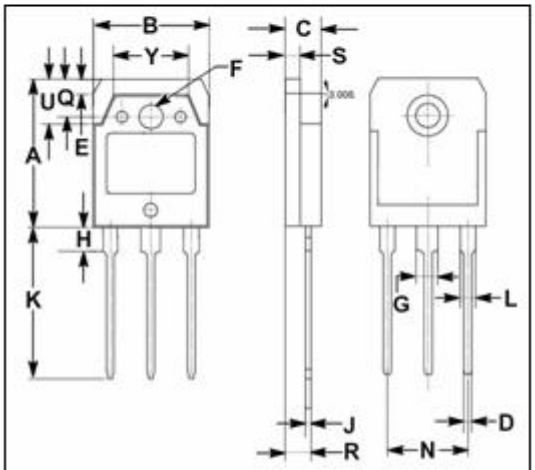


DESCRIPTION

- Low Collector Saturation Voltage-
  : $V_{CE(sat)}$= -2.0V(Min) @I_C= -5A
- Good Linearity of h_{FE}
- Complement to Type 2SD2062
- With TO-3PN package
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Power driver and general purpose applications



DIM	mm MIN	mm MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-7	A
P_C	Collector Power Dissipation @ T_C=25℃	80	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -10mA; I_B= 0	-80			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -5A; I_B= -0.5A			-2.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -5A; I_B= -0.5A			-2.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -100V; I_E= 0			-10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-10	μA
h_{FE}	DC Current Gain	I_C= -1A; V_{CE}= -5V	60		320	
f_T	Current-Gain—Bandwidth Product	I_C=-0.5A; V_{CE}= -12V		12		MHz

◆ **h_{FE}Classifications**

D	E	F
60-120	100-200	160-320